

| <del>-</del> - | Hits  | Search Text   | DB        | Time stamp |
|----------------|-------|---|-----------|------------|
| L              | nica  | Search Text   |           |            |
| Number         | 22374 | "Chemical mechanical polishing" or CMP  | USPAT;    | 2002/09/25 |
| 2              | 223/4 | CHEMICAL MECHANICAL POLLARS   | EPO; JPO; | 15:41      |
|                | ļ     |   | DERWENT;  |            |
|                |       |   | IBM TDB   |            |
| 1              | 125   | (("silicon dioxide" or "SiO.sub.2") same<br>("silicon nitride" or SiN) same             | USPAT;    | 2002/09/25 |
|                |       |   | EPO; JPO; | 15:41      |
|                |       | sacrific\$3) and ("Chemical mechanical  | DERWENT;  |            |
|                |       | polishing" or CMP)  | IBM TDB   |            |
|                | 388   |   | USPAT;    | 2002/09/25 |
|                | 300   | ("silicon nitride" or SiN) same   | EPO; JPO; | 16:46      |
|                |       | sacrific\$3   | DERWENT;  |            |
|                |       | Sacifica  | IBM TDB   | i          |
| 6              | 708   | ("Chemical mechanical polishing" or CMP)  | USPAT:    | 2002/09/25 |
|                | /08   | same sacrific\$3  | EPO; JPO; | 16:44      |
|                |       | Same Sacrificas   | DERWENT;  |            |
|                |       |   | IBM TDB   |            |
| 7              | 557   | (resist or photoresist or mask ) same   | USPAT;    | 2002/09/25 |
|                | 55/   |   | EPO; JPO; | 16:45      |
|                |       | redeposit\$4  | DERWENT;  | !          |
|                |       |   | IBM TDB   | ľ          |
| 9              | 8314  | <pre>(resist or photoresist or mask ) same<br/>(redeposit\$4 or veil or residual)</pre> | USPAT;    | 2002/09/25 |
|                |       |   | EPO; JPO; | 16:53      |
|                |       | (redeposit;4 of Veil of Tesidadi)   | DERWENT;  |            |
|                |       |   | IBM TDB   |            |
| 10             | 2047  | ("silicon dioxide" or "SiO.sub.2") and ("silicon nitride" or SiN) and sacrific\$3       | USPAT;    | 2002/09/25 |
|                | 2847  |   | EPO; JPO; | 16:47      |
|                |       | ("SITICON MICHIGE OF SIN) and successive  | DERWENT;  | ł          |
|                |       |   | IBM TDB   |            |
|                | 38    | ("Chemical mechanical polishing" or CMP)  | USPAT;    | 2002/09/25 |
|                | 38    | and ((resist or photoresist or mask)  | EPO; JPO; | 16:47      |
|                | ł     | same (redeposit\$4 or veil or residual))  | DERWENT;  | 1          |
|                |       | and (("silicon dioxide" or "SiO.sub.2")   | IBM TDB   |            |
|                |       | and ("silicon dioxide" of Sio.sub.2 / and ("silicon nitride" or SiN) and                |           |            |
|                |       |   |           |            |
| 12             | 070   | sacrific\$3) (resist or photoresist or mask ) same                                      | USPAT;    | 2002/09/25 |
|                | 279   | sidewall same (redeposit\$4 or veil or  | EPO; JPO; | 16:53      |
|                | 1     |   | DERWENT;  |            |
|                |       | residual)   | IBM TDB   | İ          |